

BAT41

V_{RRM} : 100V

FEATURES :

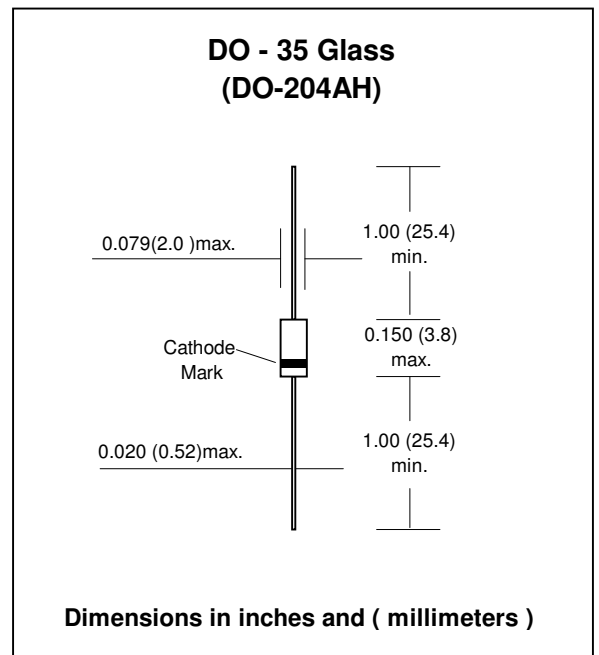
- For general purpose applications
- This diode features low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in a MiniMELF case with type designation LL41
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-35 Glass Case

Weight: approx. 0.13g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100	V
Continuous Forward Current	I _F	100 ⁽¹⁾	mA
Repetitive Peak Forward Current at tp < 1s	I _{FRM}	350 ⁽¹⁾	mA
Forward Surge Current at tp = 10 ms,	I _{FSM}	750 ⁽¹⁾	mA
Power Dissipation	P _D	400 ⁽¹⁾	W
Thermal Resistance Junction to Ambient Air	R _{θJA}	300 ⁽¹⁾	°C/W
Junction Temperature	T _J	125	°C
Ambient Operating Temperature Range	T _a	-65 to + 125	°C
Storage temperature range	T _S	-65 to + 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage ⁽²⁾	V _{(BR)R}	I _R = 100 μA	100	110	-	V
Reverse Current ⁽²⁾	I _R	V _R = 50 V	-	-	100	nA
		V _R = 50 V, T _J = 100 °C	-	-	20	μA
Forward Voltage Drop ⁽²⁾	V _F	I _F = 1mA	-	0.4	0.45	V
		I _F = 200mA	-	-	1.0	
Diode Capacitance	C _d	V _R = 0 V, f = 1MHz	-	2	-	pF
Reverse Recovery Time	T _{rr}	I _F = 10mA, I _R = 10mA, I _{rr} = 1mA, R _L = 100Ω	-	5	-	ns

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

(2) Pulse test, tp = 300μs